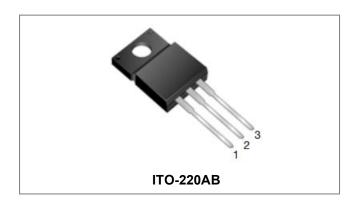






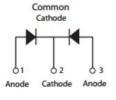
SDURF3030CT(CTR) ULTRAFAST RECTIFIER

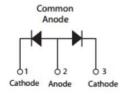


Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram





SDURF3030CT

SDURF3030CTR

Features

- · Ultra-Fast switching
- High current capability
- Low reverse leakage current
- · High surge current capability
- This is a Pb free device
- Terminals finish: 100% Pure Tin
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	300	V
Average Rectified Forward Current	I _{F (AV)}	Tc=105°C	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse, Tc=25°C	110	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V_{F1}	@ I _F = 15A, Pulse, T _J = 25℃	0.98	1.25	V
Forward Voltage Drop(Per Leg)*	V_{F1}	@ I _F = 15A, Pulse, T _J = 125℃	0.88	1.15	V
Reverse Current(Per Leg)*	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25^{\circ}C$	0.08	5.0	μΑ
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 125^{\circ}C$	0.05	1.0	mA
Reverse Recovery Time(Per Leg)	t _{rr1}	I _F =500mA, I _R =1A,and I _{rm} =250mA	40	45	ns

^{*} Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •



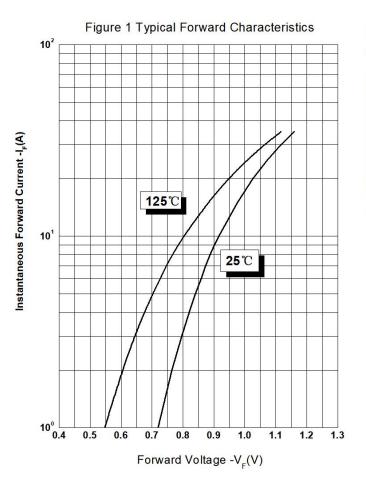




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{eJC}	DC operation	4	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves



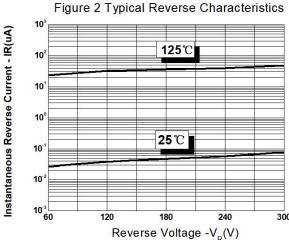
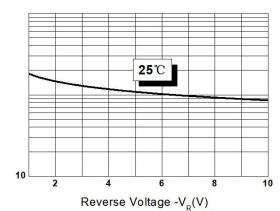


Figure 3 Typical Junction Capacitance



Junction Capacitance - CT(pF)

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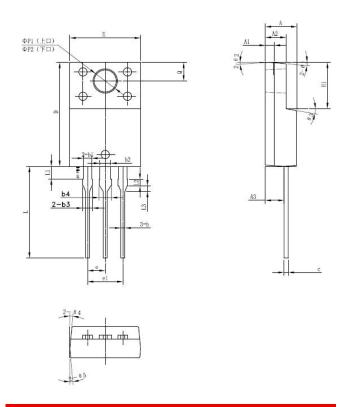
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Mechanical Dimensions ITO-220AB



SYMBOL	Millimeters				
STINIBUL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
b	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
b3	1.20	1.30	1.45		
b4	1.60	1.70	1.85		
С	0.50	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е		2.55			
e1		5.10			
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
ФР1(上□)	3.30	3.50	3.70		
ΦP2 (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

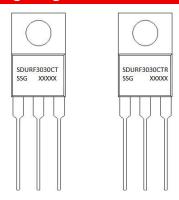
Tube Specification



Ordering Information

Device	Package	Shipping
SDURF3030CT(CTR)	ITO-220AB (Pb-Free)	50 pcs/ tube

Marking Diagram



Where XXXXX is YYWWL

 SDUR
 = Device Type

 F
 = Package type

 30
 = Forward Current (30A)

 30
 = Reverse Voltage (300V)

 CT(CTR)
 = Configuration

 SSG
 = SSG

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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